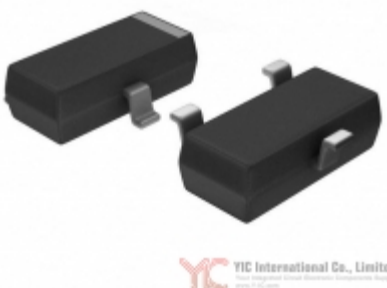

	<p>SI2321DS-T1-E3</p>
	<p>Hersteller-Teilenummer: SI2321DS-T1-E3</p>
	<p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p>
	<p>Teil der Beschreibung: MOSFET P-CH 20V 2.9A SOT-23</p>
	<p>Datenblätter:  SI2321DS-T1-E3.pdf</p>
	<p>RoHs Status: Bleifrei / RoHS-konform</p>
	<p>Lagerzustand: New original, 46338 pcs Stock Available.</p>
	<p>Liefern von: Hong Kong</p>
<p>Image may be representation. See specs for product details.</p>	<p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>

Spezifikationen

Teilenummer	SI2321DS-T1-E3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 20V 2.9A SOT-23
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	46338 pcs Stock
detaillierte Beschreibung	P-Channel 20V 2.9A (Ta) 710mW (Ta) Surface Mount
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	710mW (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	2.9A (Ta)
Rds On (Max) @ Id, Vgs	57 mOhm @ 3.3A, 4.5V
VGS (th) (Max) @ Id	900mV @ 250µA
Gate Charge (Qg) (Max) @ Vgs	13nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	715pF @ 6V
Antriebsspannung (Max Rds On, Min Rds On)	1.8V, 4.5V
Vgs (Max)	±8V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)

SI2321DS-T1-E3 ist neu im Original, Suche SI2321DS-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2321DS-T1-E3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI2321DS-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2321DS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 2.9A SOT-23</p>	 <p>SI2321-TP Micro Commercial Components (MCC) P-CHANNEL MOSFET, SOT-23 PACKAGE</p>	 <p>SI2321DS 89K SI2321DS 89K</p>	 <p>SI2321DS-T1-E3 Vishay / Siliconix MOSFET P-CH 20V 2.9A SOT-23</p>
 <p>SI2323 GMC SI2323 GMC</p>	 <p>SI2321/CJ2321 Original SOT-23</p>	 <p>SI2323CDS-T1 VISHAY SI2323CDS-T1 VISHAY</p>	 <p>SI2321DS-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 2.9A SOT-23</p>

heiße Teile

Mehr

- | | | | | |
|--------------------|--------------------|--------------------|--------------------|--------------------|
| ⊛ SI2318ADS-T1-GE3 | ↔ SI2318BDS-T1-E3 | ⇒ SI2318BDS-T1-GE3 | D SI2318CDS-T1-E3 | ⇒ SI2318CDS-T1-GE3 |
| ⊣ SI2318CDS-T1-GE3 | ⊛ SI2318DS | D SI2318DS-T1-E3 | ⇒ SI2318DS-T1-E3 | ⇒ SI2318DS-T1-GE3 |
| ⊛ SI2318DS-T1-GE3 | ⊣ SI2319ADS-T1-GE3 | ⊛ SI2319C95TF | ↔ SI2319CDS-T1-E3 | ⇒ SI2319CDS-T1-GE3 |
| D SI2319CDS-T1-GE3 | ⊛ SI2319DDS-T1-GE3 | ⊣ SI2319DS | ⊛ SI2319DS-T1-E3 | ⇒ SI2319DS-T1-E3 |
| ⇒ SI2319DS-T1-GE3 | ↔ SI2319DS-T1-GE3 | ⊛ SI2320DS | ⊣ SI2320DS-T1-E3 | ⇒ SI2320DS-T1-GE3 |
| ↔ SI2321DS-T1-E3 | ⇒ SI2321DS-T1-GE3 | D SI2321DS-T1-GE3 | ⊛ SI2323CDS-T1 | ⊣ SI2323CDS-T1-E3 |
| ⊛ SI2323CDS-T1-GE3 | D SI2323CDS-T1-GE3 | ⇒ SI2323DDS-T1-E3 | ↔ SI2323DDS-T1-GE3 | ⇒ SI2323DDS-T1-GE3 |
| ⊣ SI2323DS | ⊛ SI2323DS-T1-E3 | ↔ SI2323DS-T1-E3 | ⇒ SI2323DS-T1-GE3 | ⇒ SI2323DS-T1-GE3 |
| ⊛ SI2324DS-T1-E3 | ⊣ SI2324DS-T1-GE3 | ⊛ SI2324DS-T1-GE3 | D SI2325DS-T1-E3 | ⇒ SI2325DS-T1-E3 |
| ↔ SI2325DS-T1-GE3 | ⊛ SI2325DS-T1-GE3 | ⊣ SI2327DS-T1-E3 | ⊛ SI2327DS-T1-E3 | ⇒ SI2327DS-T1-GE3 |

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

Copyright © 2019 YIC International Co., Limited